

P-Channel 40 V (D-S) MOSFET



RoHS
COMPLIANT

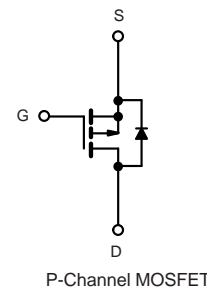
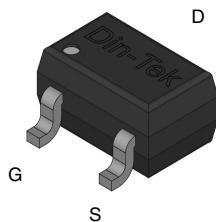
PRODUCT SUMMARY	
V_{DS} (V)	- 40
$R_{DS(on)}$ (m Ω) at $V_{GS} = -10$ V	83
$R_{DS(on)}$ (m Ω) at $V_{GS} = -4.5$ V	100
I_D (A)	- 3.6
Configuration	Single

FEATURES

- DT-Trench Power MOSFET
- AEC-Q101 Qualified^c
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

SOT-23-3L Pin Configuration

Top View



ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	- 40	V
Gate-Source Voltage		V_{GS}	± 20	
Continuous Drain Current	$T_C = 25$ °C	I_D	- 3.6	A
	$T_C = 125$ °C		- 2.6	
Continuous Source Current (Diode Conduction)		I_S	- 3.6	
Pulsed Drain Current ^a		I_{DM}	- 18	
Single Pulse Avalanche Current	L = 0.1 mH	I_{AS}	- 12	
Single Pulse Avalanche Energy		E_{AS}	7.2	
Maximum Power Dissipation ^a	$T_C = 25$ °C	P_D	3	W
	$T_C = 125$ °C		1	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to + 175	°C

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^b	R_{thJA}	166	°C/W
Junction-to-Foot (Drain)		R_{thJF}	50	

Notes

- Pulse test; pulse width 300 μ s, duty cycle 2 %.
- When mounted on 1" square PCB (FR-4 material).

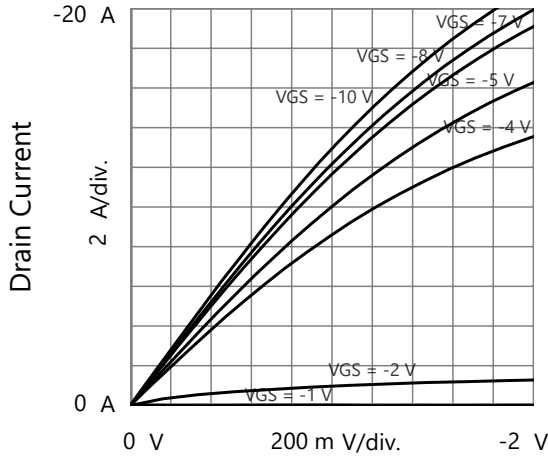
SPECIFICATIONS ($T_C = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$		-40	-	-	V
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$		-1.0	-	-2.5	
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}$	$V_{DS} = -40\text{ V}$	-	-	-1	μA
		$V_{GS} = 0\text{ V}$	$V_{DS} = -40\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	-50	
		$V_{GS} = 0\text{ V}$	$V_{DS} = -32\text{ V}, T_J = 175\text{ }^\circ\text{C}$	-	-	-150	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = -10\text{ V}$	$V_{DS} \leq -5\text{ V}$	-10	-	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$	$I_D = -3\text{ A}$	-	83	92	m Ω
		$V_{GS} = -10\text{ V}$	$I_D = -3\text{ A}, T_J = 125\text{ }^\circ\text{C}$	-	110	121	
		$V_{GS} = -10\text{ V}$	$I_D = -3\text{ A}, T_J = 175\text{ }^\circ\text{C}$	-	120	139	
		$V_{GS} = -4.5\text{ V}$	$I_D = -2.4\text{ A}$	-	100	110	
Forward Transconductance ^b	g_{fs}	$V_{DS} = -5\text{ V}, I_D = -3\text{ A}$		-	8	-	S
Dynamic^b							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}$	$V_{DS} = -25\text{ V}, f = 1\text{ MHz}$	-	682	-	μF
Output Capacitance	C_{oss}			-	448	-	
Reverse Transfer Capacitance	C_{rss}			-	353	-	
Total Gate Charge ^c	Q_g	$V_{GS} = -10\text{ V}$	$V_{DS} = -20\text{ V}, I_D = -3\text{ A}$	-	10.5	16	nC
Gate-Source Charge ^c	Q_{gs}			-	1.8	-	
Gate-Drain Charge ^c	Q_{gd}			-	2.6	-	
Gate Resistance	R_g	f = 1 MHz		-	20	-	Ω
Turn-On Delay Time ^c	$t_{d(on)}$	$V_{DD} = -20\text{ V}, R_L = 6.7\text{ }\Omega$ $I_D \equiv -3\text{ A}, V_{GEN} = -10\text{ V}, R_g = 1\text{ }\Omega$	-	5	8	ns	
Rise Time ^c	t_r		-	11	17		
Turn-Off Delay Time ^c	$t_{d(off)}$		-	19	29		
Fall Time ^c	t_f		-	8	12		
Source-Drain Diode Ratings and Characteristics^b							
Pulsed Current ^a	I_{SM}			-	-	-18	A
Forward Voltage	V_{SD}	$I_F = -1.5\text{ A}, V_{GS} = 0$		-	-0.8	-1.2	V

Notes

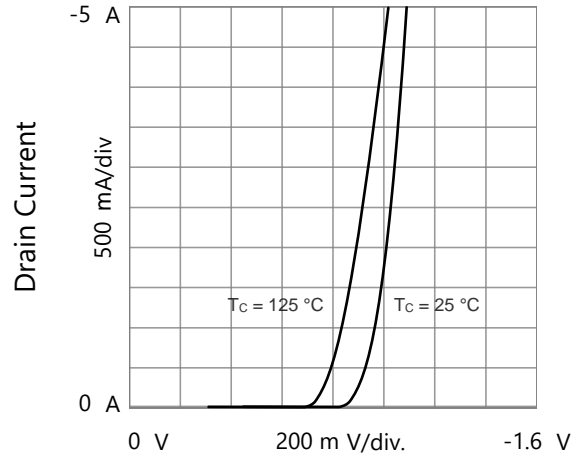
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

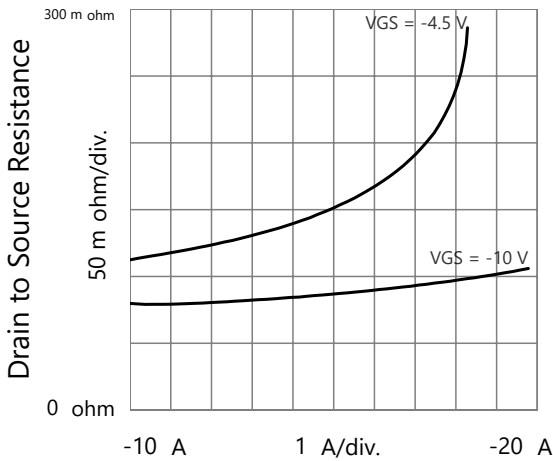
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



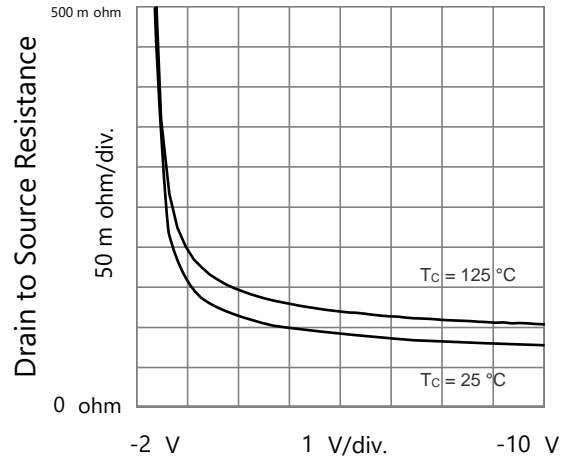
Drain to Source Voltage
Output Characteristics



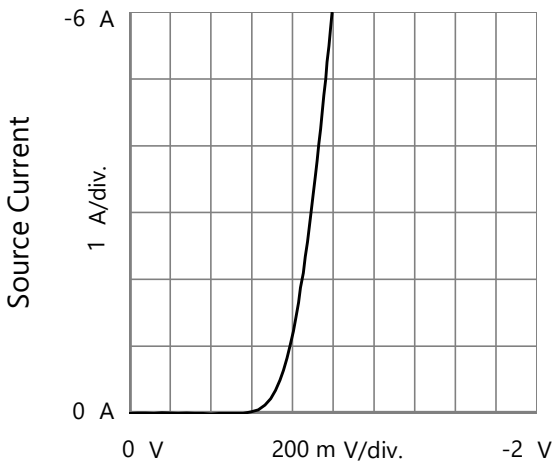
Gate to Source Voltage
Transfer Characteristics



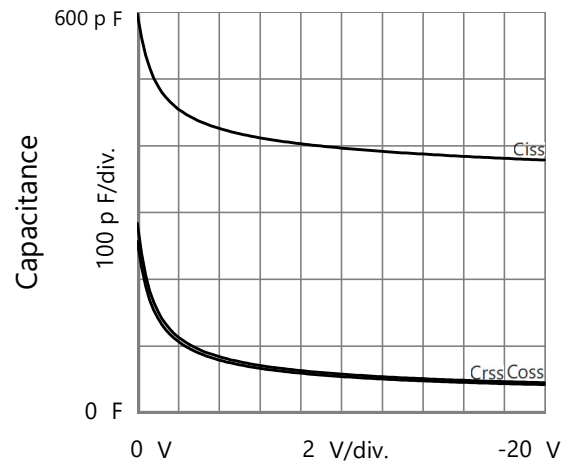
Drain Current
Drain to Source Resistance vs. Drain Current



Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage

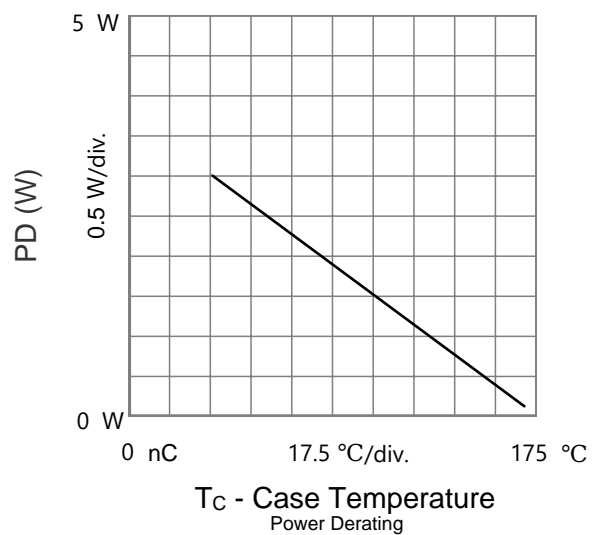
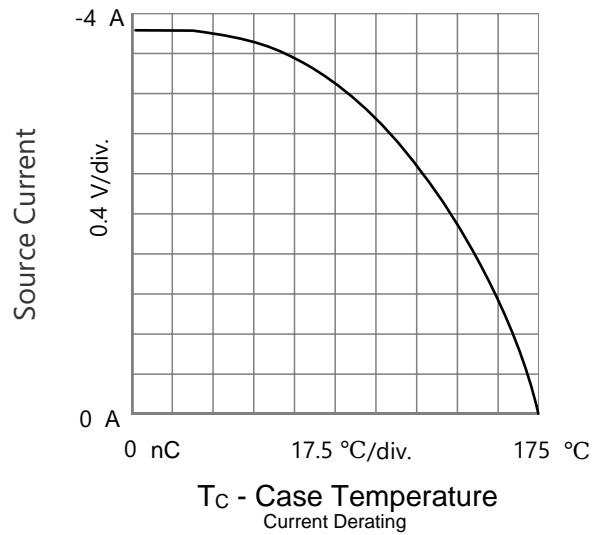
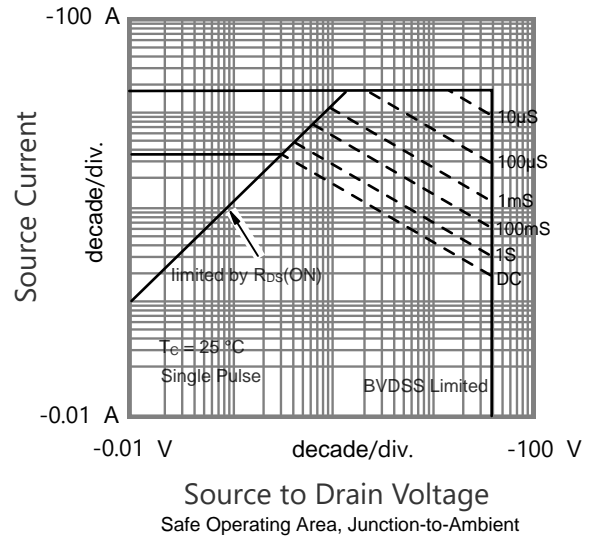
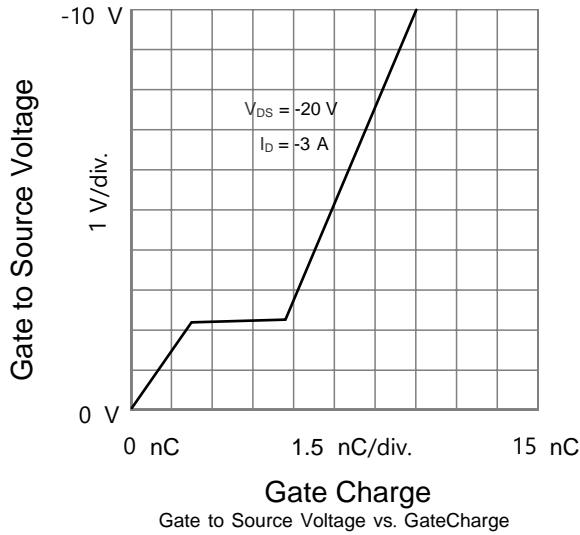


Source to Drain Voltage
Body Diode Forward Characteristics

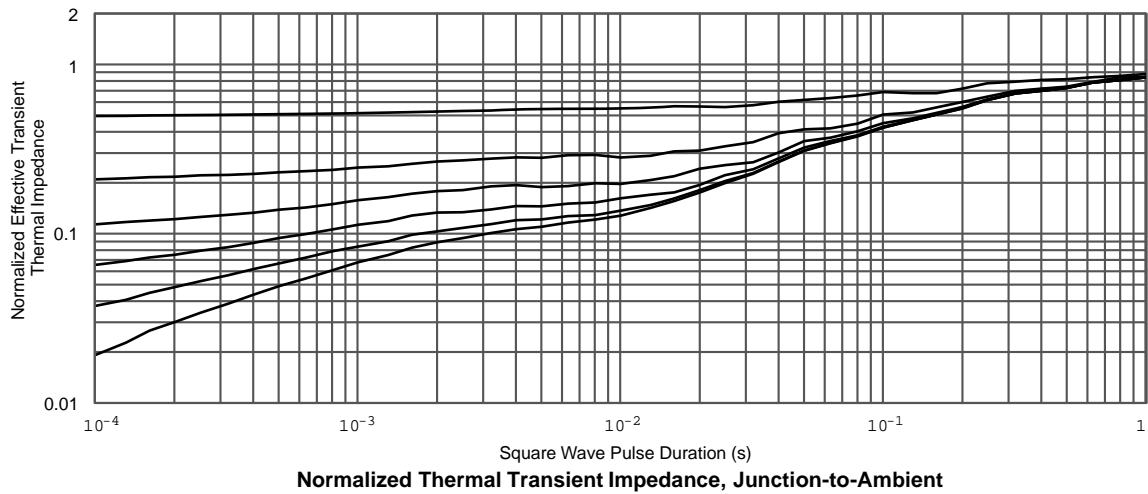


Drain to Source Voltage
Capacitances

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



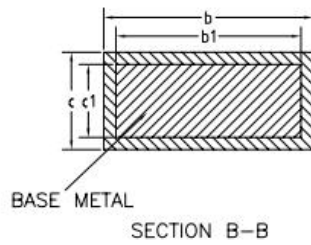
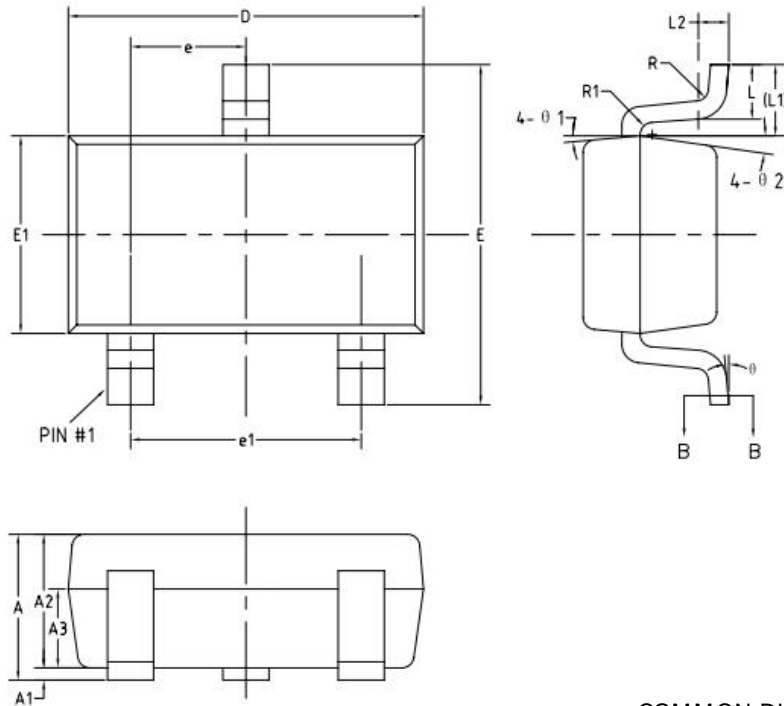
THERMAL RATINGS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)
 are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

SOT-23-3L PACKAGE OUTLINE



COMMON DIMENSIONS
(UNITS OF MEASURE= MILLIMETER)

SYMBOL	MIN	TYP	MAX
A	-	-	1.50
A1	0.00	-	0.18
A2	0.85	1.10	1.35
A3	0.58	0.65	0.72
b	0.23	-	0.53
b1	0.20	0.40	0.50
c	0.09	-	0.22
c1	0.08	0.13	0.21
D	2.78	2.95	3.10
E	2.58	2.80	3.03
E1	1.55	1.65	1.78
e	0.83	0.95	1.07
e1	1.78	1.90	2.02
L	0.28	0.45	0.62
L1	0.59REF		
L2	0.25BSC		
R	0.04	-	-
R1	0.04	-	0.21
θ	0°	-	8°
$\theta 1$	8°	10°	12°
$\theta 2$	8°	10°	12°

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